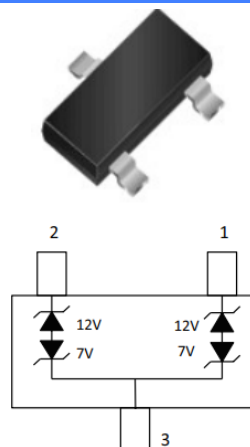


ESDSM712

Features

- SOT-23 package
- Operating voltage: -7V~12V
- Low leakage current
- Low clamping voltage
- Response time is typically < 1ns
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$

Circuit Diagram



Description

The ESDSM712 TVS Diode Array is designed to protect RS-485 applications with asymmetrical working voltages (-7V to 12V) from damage due to electrostatic discharge (ESD), electrical fast transients (EFT), and lightning induced surges

Applications

- RS-485
- Fieldbus
- Modbus

Absolute Maximum Ratings

Tamb=25°C unless otherwise specified

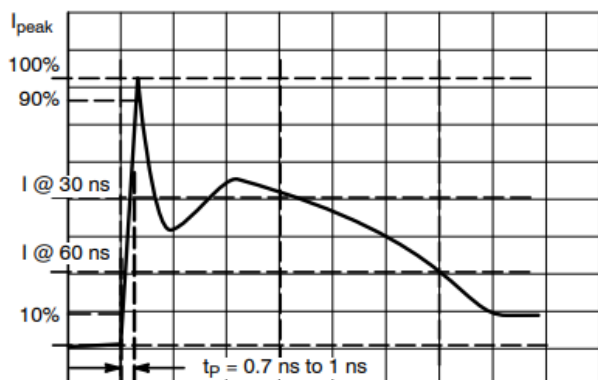
Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20 μs)	P _{pp}	400	W
ESD per IEC 61000-4-2 (Air)	V _{ESD}	± 30	KV
ESD per IEC 61000-4-2 (Contact)		± 30	
Storage Temperature Range	T _{STJ}	-55 to +150	°C
Operating Temperature Range	T _J	-55 to +125	°C

Electrical Characteristics

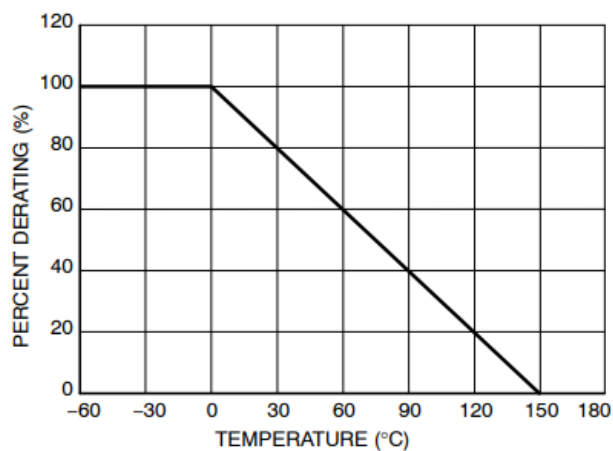
TA=25°C unless otherwise specified

Symbol	Parameter	Conditions	Pin 1 or Pin2 to Pin3			Pin3 to Pin 1 or Pin2			Units
			Min	Typ	Max	Min	Typ	Max	
V _{RWM}	Reverse Working Peak Voltage	-			12			7	V
V _{BR}	Reverse Breakdown Voltage	I _T = 1mA	13.3			7.5			V
I _R	Reverse Current	@V _{RWM}			0.1			0.1	μA
V _C	Clamping Voltage	I _{PP} =1A, t _P =8/20 μs			17			10.5	V
V _C	Clamping Voltage	@I _{PP} , t _P =8/20 μs			24@15A			20@20A	V
C _D	Diode Capacitance	V _R = 0V, f = 1MHz		75			75		pF

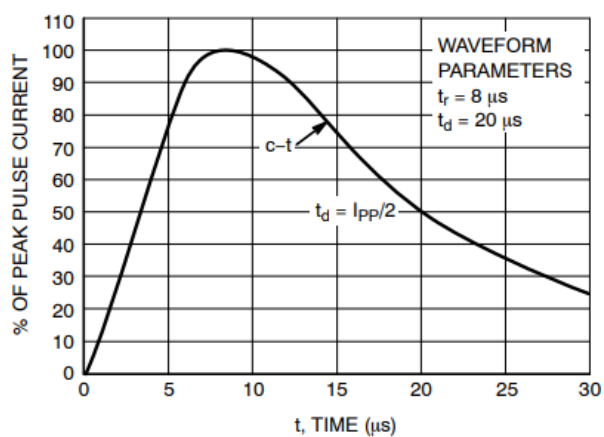
Characteristic Curves



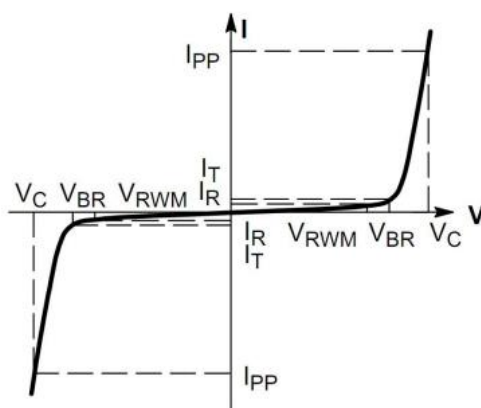
IEC61000-4-2 Pulse Waveform



Power Derating Curve

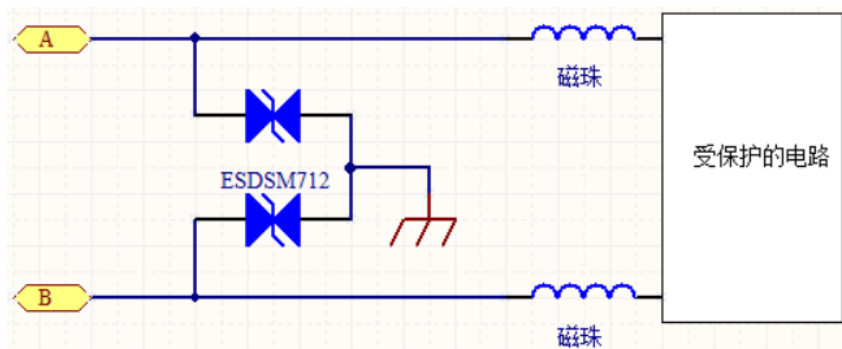


8/20μs Pulse Waveform

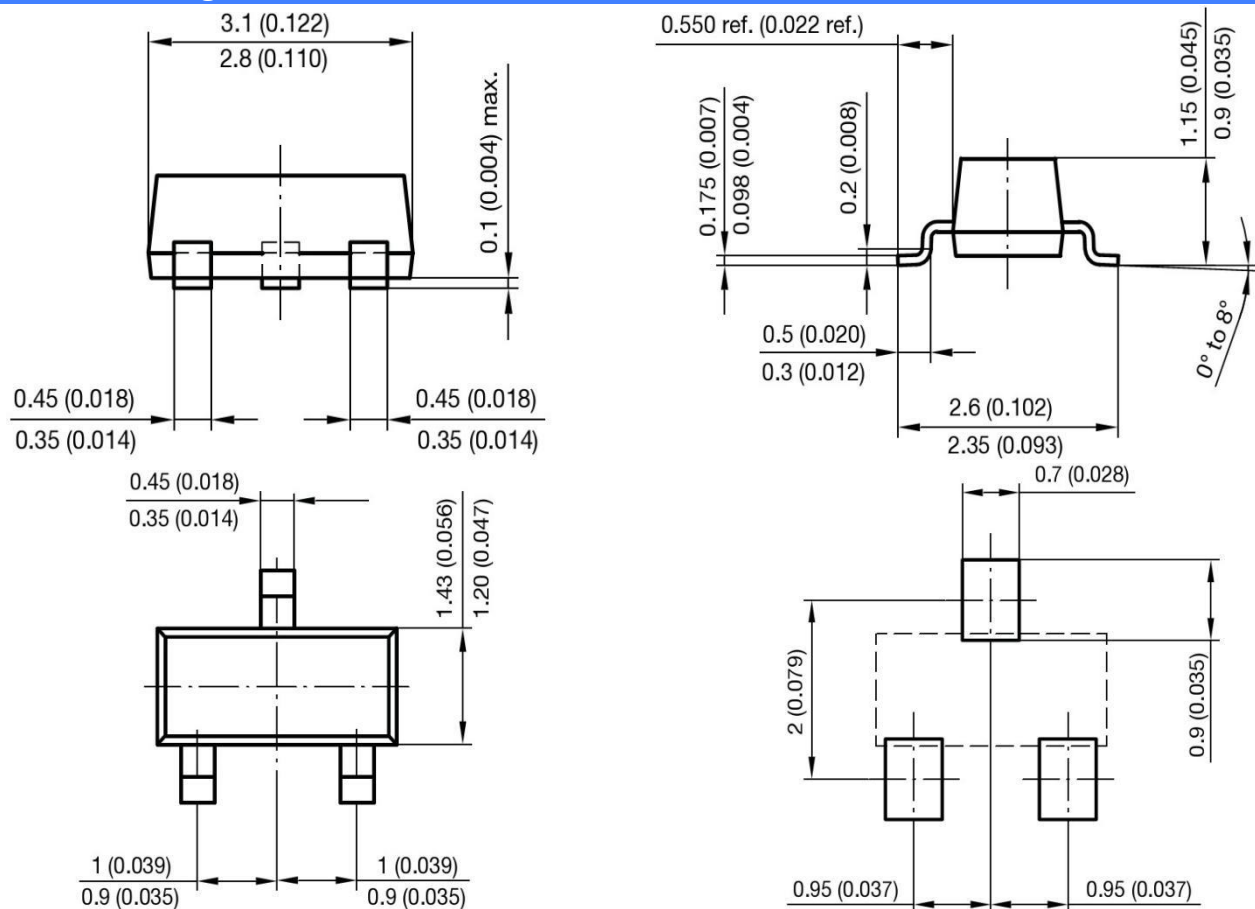


V-I Characteristics for Bidirectional Diode

RS-485 Application Example



SOT-23 Package Outline & Dimensions



Mounting Pad Layout

Disclaimer

Specifications are subject to change without notice.

The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time.

Users should verify actual device performance in their specific applications.